Abstracts

Plated Source Bridge (PSB) GaAs Power FET with Improved Reliability

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T. Suzuki, M. Kobiki, M. Wataze, K. Segawa and M. Irie. "Plated Source Bridge (PSB) GaAs Power FET with Improved Reliability." 1981 MTT-S International Microwave Symposium Digest 81.1 (1981 [MWSYM]): 34-36.

Flip chip type GaAs power FET having a plated source bridge (PSB) structure has been developed. Thermal resistance is improved by 2° C/W for a device with total gate width of 2400µ. This improvement results in 2 times increase of the device MTTF. At the channel temperature of 150°C, MTTF more than 10 /sup 7/ hours is estimated by accelerated operation life tests.

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